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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA AB					

FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
AH AK			

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TN	P	Nakamura et al., "Present Status of InGaN/GaN/AlGaIn based laser diodes", Proceedings of the Second International Conference on Nitride Semiconductors - ICNS '97 - pp.444-446.
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